Kirill V Chizh

List of Publications by Year in descending order

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		1478505	1372567
19	108	6	10
papers	citations	h-index	g-index
10	10	10	76
19	19	19	76
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	IR absorptance of thin carbon multi-walled nanotubes layers. Optical Materials, 2022, 126, 112151.	3.6	1
2	Diffusion processes in germanium and silicon films grown on Si3N4 substrates. Solar Energy Materials and Solar Cells, 2021, 230, 111231.	6.2	1
3	Low-temperature formation of platinum silicides on polycrystalline silicon. Journal of Alloys and Compounds, 2020, 843, 155908.	5.5	1
4	Diffusion of hydrogen atoms in silicon layers deposited from molecular beams on dielectric substrates. Materials Science in Semiconductor Processing, 2019, 99, 78-84.	4.0	5
5	Raman Scattering Enhancement Using Au/SiGe and Au/Ge Nanostructures. Journal of Applied Spectroscopy, 2019, 86, 72-75.	0.7	3
6	Room-temperature formation of Pt ₃ Si/Pt ₂ Si films on poly-Si substrates. Journal of Physics: Conference Series, 2017, 816, 012011.	0.4	4
7	Silicon-germanium and platinum silicide nanostructures for silicon based photonics. , 2017, , .		5
8	Metal silicide/Si thin-film Schottky-diode bolometers. , 2015, , .		5
9	Pt silicide/poly-Si Schottky diodes as temperature sensors for bolometers. Journal of Applied Physics, 2015, 117, .	2.5	12
10	The Study of Morphology and Photoelectric Sensitivity of Low-Temperature Ge/Si Heterostructures with Ge Quantum Dots. Journal of Nanoelectronics and Optoelectronics, 2015, 9, 734-737.	0.5	0
11	Submillimeter Quasioptical Spectroscopy of Multilayer Conducting and Superconducting Systems. Radiophysics and Quantum Electronics, 2014, 56, 620-627.	0.5	2
12	Metal silicide/poly-Si Schottky diodes for uncooled microbolometers. Nanoscale Research Letters, 2013, 8, 177.	5.7	11
13	Application of hydrogenation to low-temperature cleaning of the Si(001) surface in the processes of molecular-beam epitaxy: Investigation by scanning tunneling microscopy, reflected high-energy electron diffraction, and high resolution transmission electron microscopy. Journal of Applied Physics. 2012, 112, 014311.	2.5	3
14	Ge/Si(001) heterostructures with dense arrays of Ge quantum dots: morphology, defects, photo-emf spectra and terahertz conductivity. Nanoscale Research Letters, 2012, 7, 414.	5.7	11
15	Phase transition on the Si(001) clean surface prepared in UHV MBE chamber: a study by high-resolution STM and in situ RHEED. Nanoscale Research Letters, 2011, 6, 218.	5.7	16
16	Phase transition between (2 \tilde{A} — 1) and c(8 \tilde{A} — 8) reconstructions observed on the Si(001) surface around 600 \hat{A} °C. JETP Letters, 2010, 92, 310-314.	1.4	11
17	Absorption of terahertz radiation in Ge/Si(001) heterostructures with quantum dots. JETP Letters, 2010, 92, 793-798.	1.4	6
18	Capacitance investigation of Ge nanoclusters on a silicon (001) surface grown by MBE at low temperatures. Physica B: Condensed Matter, 2009, 404, 4705-4707.	2.7	2

#	Article	lF	CITATIONS
19	The role of interdiffusion and spatial confinement in the formation of resonant raman spectra of Ge/Si(100) heterostructures with quantum-dot arrays. Physics of the Solid State, 2008, 50, 1970-1977.	0.6	9